

INDIAN INSTITUTE OF TECHNOLOGY BOMBAY

MATERIALS MANAGEMENT DIVISION Powai, Mumbai 400076.

Ref. No. 2021-22/27(PR. No. 1000019956)

Rfx. No. 6100000880

Technical Specification of Avalanche Photo Diode (APD)

- 1.Photon Detection Efficiency (PDE)-The APD should have a PDE of more than 60 % at 650 nm.
- 2 The APD should have a PDE of more than 60 % at 785 nm.
- 3. The APD should have a PDE of more than 30 % at 830 nm.
- 4. Minimum dead time- It should be less than 25 ns.
- 5.Dark count-less than 110 counts/sec.
- 6. Active area of minimum 170 μm.
- 7. After pulsing probability should be less than 1 %.
- 8. output pulse width: 10ns
- 9. Fiber coupling facility should be there.
- 10. Power Supply should be included.
- 11. Warranty -1 year